## ZXTP25015DFH

## 15V, SOT23, PNP medium power transistor

Summary
$B V_{\text {CEO }}>-15 V$
$B V_{E C O}>-3 V$
$I_{C(\text { cont) })}=-4 \mathrm{~A}$
$R_{\text {CE(sat) }}=33 \mathrm{~m} \Omega$
$\mathrm{V}_{\mathrm{CE}(\text { sat })}<-55 \mathrm{mV}$ @ 1A
$P_{D}=1.25 \mathrm{~W}$

## Complementary part number ZXTN25015DFH

## Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

## Features

- High power dissipation SOT23 package

- High peak current
- Low saturation voltage
- 15 V forward blocking voltage
- 3 V reverse blocking voltage


## Applications

- MOSFET and IGBT gate driving
- DC - DC converters
- Motor drive
- High side driver
- Load disconnect switch


Pinout - top view

## Ordering information

| Device | Reel size <br> (inches) | Tape width <br> $(\mathbf{m m})$ | Quantity per reel |
| :--- | :---: | :---: | :---: |
| ZXTP25015DFHTA | 7 | 8 | 3,000 |

## Device marking

1A7

## Absolute maximum ratings

| Parameter | Symbol | Limit | Unit |
| :--- | :---: | :---: | :---: |
| Collector-base voltage | $\mathrm{V}_{\mathrm{CBO}}$ | -15 | V |
| Collector-emitter voltage | $\mathrm{V}_{\mathrm{CEO}}$ | -15 | V |
| Emitter-collector voltage (reverse blocking) | $\mathrm{V}_{\text {ECO }}$ | -3 | V |
| Emitter-base voltage | $\mathrm{V}_{\text {EBO }}$ | -7 | V |
| Continuous collector current ${ }^{(\mathrm{b})}$ | $\mathrm{I}_{\mathrm{C}}$ | -4 | A |
| Base current | $\mathrm{I}_{\mathrm{B}}$ | -1 | A |
| Peak pulse current | $\mathrm{I}_{\mathrm{CM}}$ | -10 | A |
| Power dissipation at $\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}^{\text {(a) }}$ | $\mathrm{P}_{\mathrm{D}}$ | 0.73 | W |
| Linear derating factor |  | 5.84 | $\mathrm{~mW} /{ }^{\circ} \mathrm{C}$ |
| Power dissipation at $\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}^{\text {(b) }}$ | $\mathrm{P}_{\mathrm{D}}$ | 1.05 | W |
| Linear derating factor |  | 8.4 | $\mathrm{~mW} /{ }^{\circ} \mathrm{C}$ |
| Power dissipation at $\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}^{\text {(c) }}$ | $\mathrm{P}_{\mathrm{D}}$ | 1.25 | W |
| Linear derating factor |  | 9.6 | $\mathrm{~mW} /{ }^{\circ} \mathrm{C}$ |
| Power dissipation at $\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}^{\text {(d) }}$ | $\mathrm{P}_{\mathrm{D}}$ | 1.81 | W |
| Linear derating factor |  | 14.5 | $\mathrm{~mW} /{ }^{\circ} \mathrm{C}$ |
| Operating and storage temperature range | $\mathrm{T}_{\mathrm{j}} \mathrm{T}_{\mathrm{stg}}$ | -55 to 150 | ${ }^{\circ} \mathrm{C}$ |

## Thermal resistance

| Parameter | Symbol | Limit | Unit |
| :--- | :---: | :---: | :---: |
| Junction to ambient $^{(\mathrm{a})}$ | $\mathrm{R}_{\Theta J A}$ | 171 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction to ambient $^{(\mathrm{b})}$ | $\mathrm{R}_{\Theta J A}$ | 119 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction to ambient $^{(\mathrm{c})}$ | $\mathrm{R}_{\Theta J A}$ | 100 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction to ambient $^{\text {(d) }}$ | $\mathrm{R}_{\text {ӨJA }}$ | 69 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

## NOTES:

(a) For a device surface mounted on $15 \mathrm{~mm} \times 15 \mathrm{~mm} \times 1.6 \mathrm{~mm}$ FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions.
(b) Mounted on $25 \mathrm{~mm} \times 25 \mathrm{~mm} \times 1.6 \mathrm{~mm}$ FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
(c) Mounted on $50 \mathrm{~mm} \times 50 \mathrm{~mm} \times 1.6 \mathrm{~mm}$ FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
(d) As (c) above measured at $\mathrm{t}<5$ secs.

## ZXTP25015DFH

## Characteristics



## ZXTP25015DFH

## Electrical characteristics (at $\mathrm{T}_{\mathrm{amb}}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ unless otherwise stated)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Collector-base breakdown voltage | $\mathrm{BV}_{\mathrm{CBO}}$ | -15 | -35 |  | V | $\mathrm{I}_{\mathrm{C}}=-100 \mu \mathrm{~A}$ |
| Collector-emitter breakdown voltage (base open) | $\mathrm{BV}_{\text {CEO }}$ | -15 | -30 |  | V | $I_{C}=-10 m A^{(*)}$ |
| Emitter-base breakdown voltage | $\mathrm{BV}_{\mathrm{EBO}}$ | -7 | -8.4 |  | V | $\mathrm{I}_{\mathrm{E}}=-100 \mu \mathrm{~A}$ |
| Emitter-collector breakdown voltage (base open) | $\mathrm{BV}_{\mathrm{ECO}}$ | -3 | -8.2 |  | V | $I_{E}=-100 \mu A^{(*)}$ |
| Collector-base cut-off current | $\mathrm{I}_{\text {CBO }}$ |  | <-1 | $\begin{aligned} & -50 \\ & -20 \end{aligned}$ | $\begin{aligned} & \mathrm{nA} \\ & \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{CB}}=-12 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{CB}}=-12 \mathrm{~V}, \mathrm{~T}_{\mathrm{amb}}=100^{\circ} \mathrm{C} \end{aligned}$ |
| Emitter-base cut-off current | $\mathrm{I}_{\text {EBO }}$ |  | <-1 | -50 | nA | $\mathrm{V}_{\mathrm{EB}}=-5.6 \mathrm{~V}$ |
| Collector-emitter saturation voltage | $\mathrm{V}_{\text {CE(sat) }}$ |  | $\begin{aligned} & \hline-45 \\ & -110 \\ & -130 \\ & -160 \\ & -165 \end{aligned}$ | $\begin{aligned} & -55 \\ & -150 \\ & -175 \\ & -210 \\ & -220 \end{aligned}$ | mV <br> mV <br> mV <br> mV <br> mV | $\begin{aligned} & I_{C}=-1 A, I_{B}=-100 m A^{(*)} \\ & I_{C}=-1 A, I_{B}=-10 m A^{(*)} \\ & I_{C}=-2 A, I_{B}=-40 m A^{(*)} \\ & I_{C}=-4 A, I_{B}=-200 m A^{(*)} \\ & I_{C}=-5 A, I_{B}=-500 m A^{(*)} \end{aligned}$ |
| Base-emitter saturation voltage | $\mathrm{V}_{\mathrm{BE} \text { (sat) }}$ |  | -930 | -1050 | mV | $I_{C}=-4 A, I_{B}=-200 m A^{(*)}$ |
| Base-emitter turn-on voltage | $V_{\text {BE(on) }}$ |  | -810 | -900 | mV | $\mathrm{I}_{\mathrm{C}}=-4 \mathrm{~A}, \mathrm{~V}_{C E}=-2 \mathrm{~V}^{(*)}$ |
| Static forward current transfer ratio | $\mathrm{h}_{\text {FE }}$ | $\begin{gathered} \hline 300 \\ 200 \\ 90 \end{gathered}$ | $\begin{gathered} 450 \\ 315 \\ 145 \\ 30 \end{gathered}$ | 900 |  | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=-10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=-2 \mathrm{~V}^{(*)} \\ & \mathrm{I}_{\mathrm{C}}=-1 \mathrm{~A}, \mathrm{~V}_{C E}=-2 \mathrm{~V}^{(*)} \\ & \mathrm{I}_{\mathrm{C}}=-4 \mathrm{~A}, \mathrm{~V}_{C E}=-2 \mathrm{~V}^{(*)} \\ & \mathrm{I}_{\mathrm{C}}=-10 \mathrm{~A}, \mathrm{~V}_{C E}=-2 \mathrm{~V}^{(*)} \end{aligned}$ |
| Transition frequency | $\mathrm{f}_{\mathrm{T}}$ |  | 295 |  | MHz | $\begin{aligned} & I_{C}=-50 \mathrm{~mA}, V_{C E}=-10 \mathrm{~V} \\ & \mathrm{f}=100 \mathrm{MHz} \end{aligned}$ |
| Output capacitance | $\mathrm{C}_{\text {OBO }}$ |  | 25 | 30 | pF | $\mathrm{V}_{C B}=-10 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}^{(*)}$ |
| Delay time | $\mathrm{t}_{\mathrm{d}}$ |  | 33.8 |  | ns | $\mathrm{V}_{C C}=-15 \mathrm{~V}$. |
| Rise time | $\mathrm{t}_{\mathrm{r}}$ |  | 43.5 |  | ns | $I_{C}=-750 \mathrm{~mA},$ |
| Storage time | $\mathrm{t}_{\mathrm{s}}$ |  | 196 |  | ns |  |
| Fall time | $\mathrm{t}_{\mathrm{f}}$ |  | 51.7 |  | ns |  |

NOTES:
(*) Measured under pulsed conditions. Pulse width $\leq 300 \mu s$; duty cycle $\leq 2 \%$.

## ZXTP25015DFH

## Typical characteristics







## Package outline - SOT23



| Dim. | Millimeters |  |  |  | Dim. | Millimeters |  | Inches |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min. | Max. | Min. | Max. |  | Min. | Max. | Min. | Max. |
| A | - | 1.12 | - | 0.044 | e1 |  | OM | 0.075 | NOM |
| A1 | 0.01 | 0.10 | 0.0004 | 0.004 | E | 2.10 | 2.64 | 0.083 | 0.104 |
| b | 0.30 | 0.50 | 0.012 | 0.020 | E1 | 1.20 | 1.40 | 0.047 | 0.055 |
| C | 0.085 | 0.20 | 0.003 | 0.008 | L | 0.25 | 0.60 | 0.0098 | 0.0236 |
| D | 2.80 | 3.04 | 0.110 | 0.120 | L1 | 0.45 | 0.62 | 0.018 | 0.024 |
| e | 0.95 NOM |  | 0.037 NOM |  | - | - | - | - | - |

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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